

## Day-26

### → Point defects

Equilibrium concentration of vacancies in a metallic crystal

$$\exp\left(-\frac{\Delta F_v}{RT}\right) \rightarrow \text{different for different materials}$$

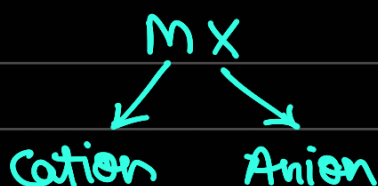
### → Local Electroneutrality Condition (ENC)

+ve defect compensated by -ve defect

Kroger-Vink Notation

### → Stoichiometric defect -

Anion-cation ratio is maintained



consider a region of the perfect crystal



10 vacancies of O

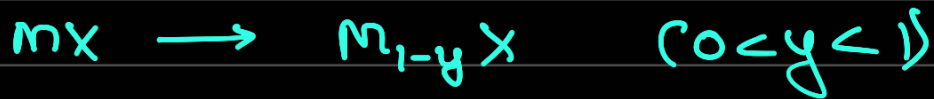
10 vacancies of Fe



→ Another way: 10 vacancies of oxygen  
these 10 oxygen atoms can

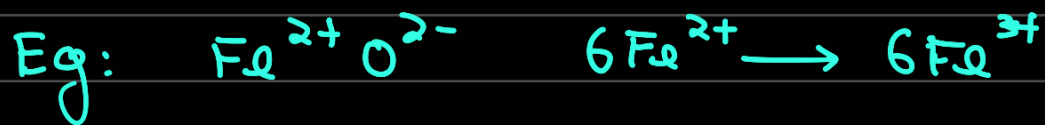
go to interstitial positions  
(Also a stoichiometric defect)

→ Non-stoichiometric defect



100 M and 100 X

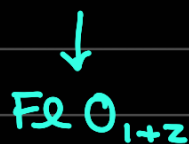
Create 10 vacancies of M ( $y = 0.1$ )



→ Interaction between ionic defects and electronic defects

→ Interaction with environment (other than temp. equilibrium)

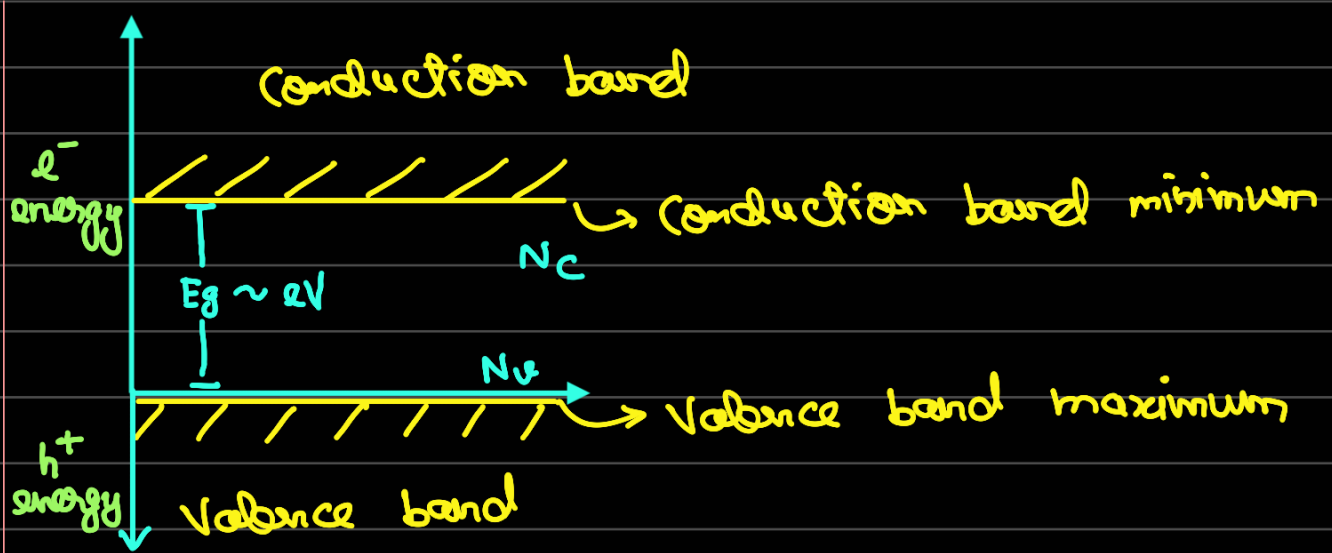
O → interstitial site



→ Electron as a defect

Band gap → There are certain values of energy it cannot assume.

Flat Band diagram



## Effective density of States

At  $T = 0\text{ K}$ , some  $n\ e^-$

$$n \rightarrow \text{VBM} \rightarrow E = 0$$

$$\text{OR } m\ e^- \rightarrow \text{CBM} \rightarrow E = (n-m)0 + mE_g$$

$$(n-m)\ e^- \rightarrow \text{VBM} = mE_g > 0$$

If  $T > 0$

Energy available  $\rightarrow$  Thermal energy  
 $= kT$

when  $T \approx 300\text{ K}$ ,  $kT \approx 25\text{ meV}$

$n\ e^-$  at  $\text{VBM} \rightarrow \text{I}$

$(n-m)\ e^-$  at  $\text{VBM} + m$  at  $\text{CBM} \rightarrow \text{II}$

at  $T > 0$

$n\ e^- \rightarrow 2^n$  states

$T = 0\text{ K}$  (perfect state)

$$\Delta F = \Delta U - T\Delta S$$

$T > 0$  (defect)

Any  $e^-$  in c.B. is considered a defect

(electron) hole  $\rightarrow h$

$$Ni \rightleftharpoons [ + ] + [ - ]$$

$$e(vB) + h(cB) \rightleftharpoons [e(cB)] + [h(vB)]$$